

Automotive N-Channel 80 V (D-S) 175 °C MOSFET

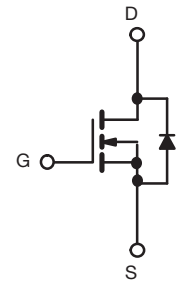
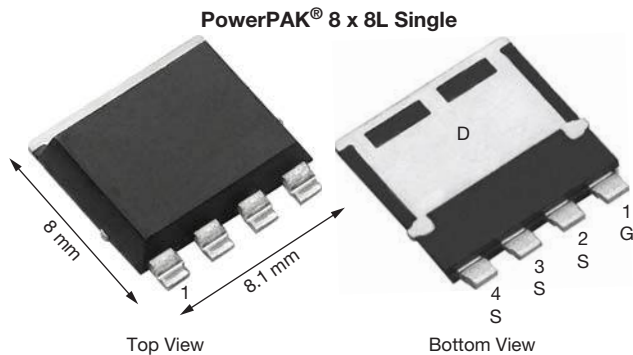


RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY	
V_{DS} (V)	80
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.003
I_D (A)	150
Configuration	Single
Package	PowerPAK 8 x 8L

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Fully lead (Pb)-free device
- Thin 1.9 mm height
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	80	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	I_D	$T_C = 25$ °C	A	
		$T_C = 125$ °C		87
Continuous Source Current (Diode conduction)	I_S	124	A	
Pulsed Drain Current ^a	I_{DM}	210		
Single Pulse Avalanche Current	I_{AS}	L = 0.1 mH	53	
				Single Pulse Avalanche Energy
Maximum Power Dissipation	P_D	$T_C = 25$ °C	136	W
		$T_C = 125$ °C	45	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C	
Soldering Recommendations (Peak temperature) ^{c, d}		260		

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	50	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.1	

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$		80	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.5	3	3.5	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 80\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = 80\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 80\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	500	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	50	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}$	-	0.0024	0.0030	Ω
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.0048	
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.0060	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		-	82	-	S
Dynamic ^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	6900	8625	pF
Output Capacitance	C_{oss}			-	3655	4570	
Reverse Transfer Capacitance	C_{rss}			-	250	311	
Total Gate Charge ^c	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 40\text{ V}, I_D = 10\text{ A}$	-	82	144	nC
Gate-Source Charge ^c	Q_{gs}			-	11	-	
Gate-Drain Charge ^c	Q_{gd}			-	21	-	
Gate Resistance	R_g	$f = 1\text{ MHz}$		0.4	0.8	1.2	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 40\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		-	19	30	ns
Rise Time ^c	t_r			-	7.3	11	
Turn-Off Delay Time ^c	$t_{d(off)}$			-	40	60	
Fall Time ^c	t_f			-	15	23	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I_{SM}			-	-	210	A
Forward Voltage	V_{SD}	$I_F = 40\text{ A}, V_{GS} = 0\text{ V}$		-	0.7	1.2	V

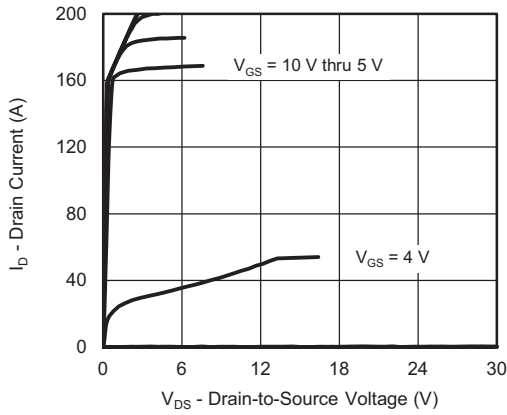
Notes

- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

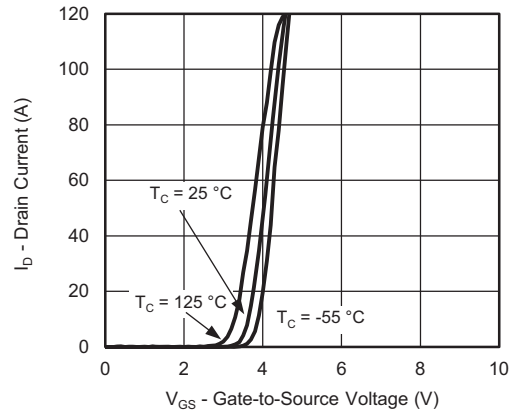
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



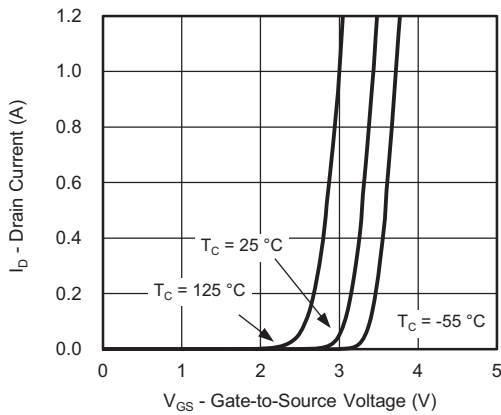
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



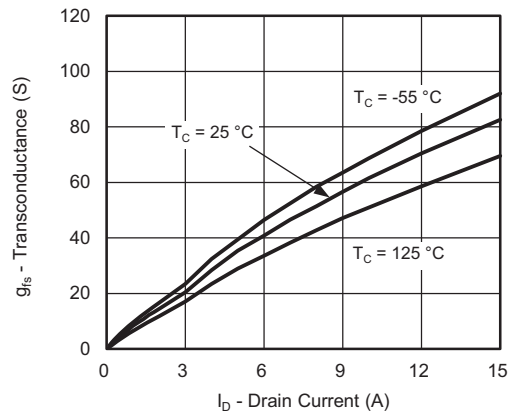
Output Characteristics



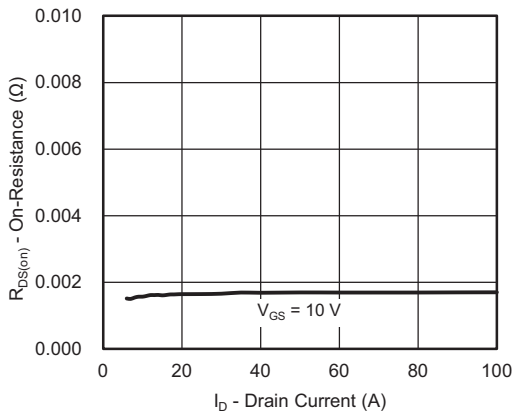
Transfer Characteristics



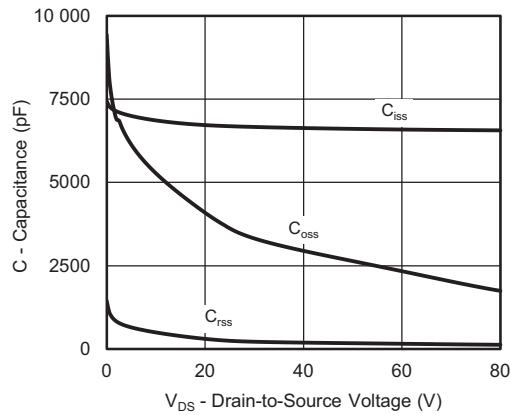
Transfer Characteristics



Transconductance



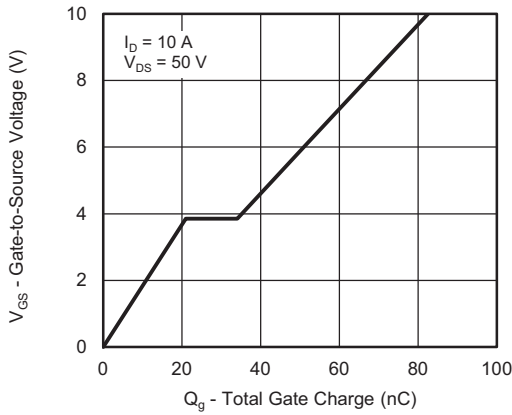
On-Resistance vs. Drain Current



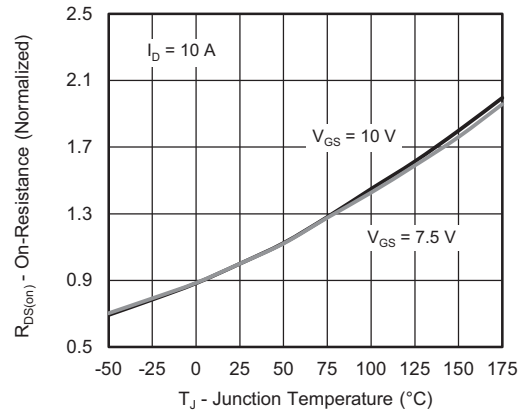
Capacitance



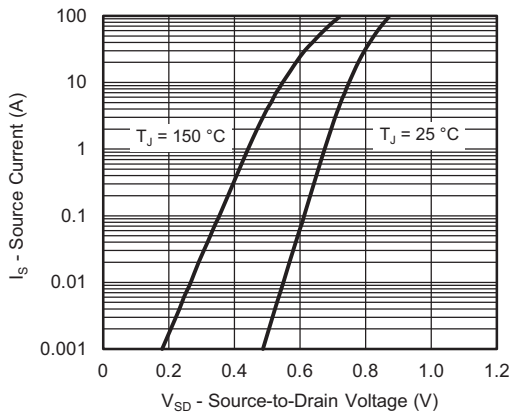
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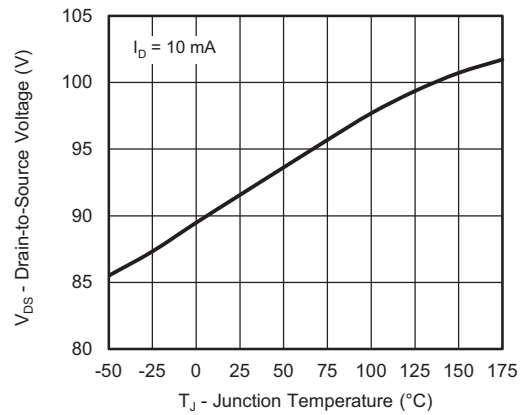
Gate Charge



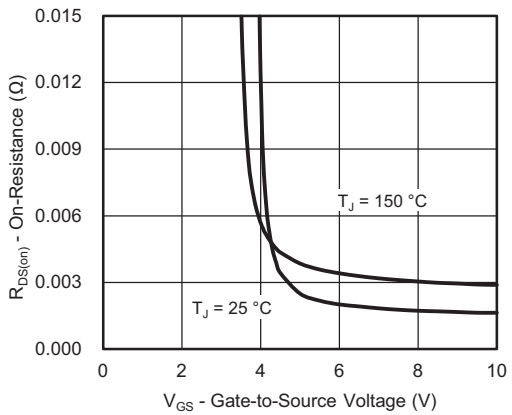
On-Resistance vs. Junction Temperature



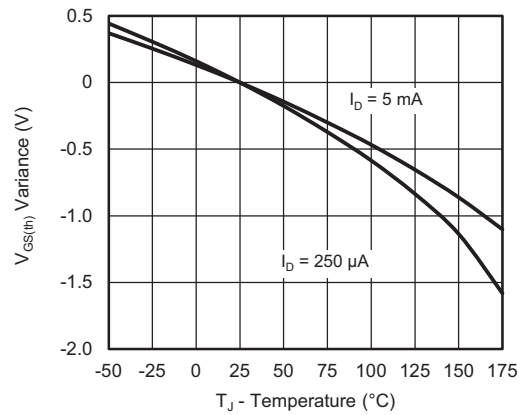
Source Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature

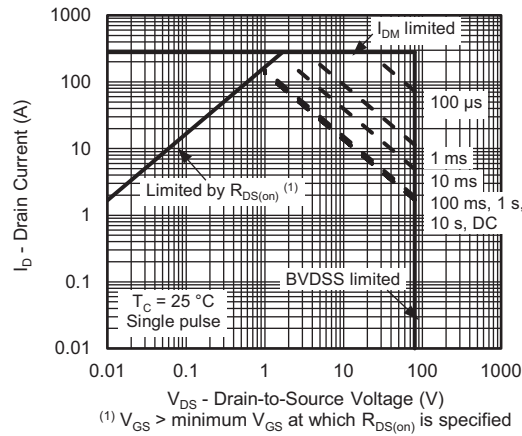


On-Resistance vs. Gate-to-Source Voltage



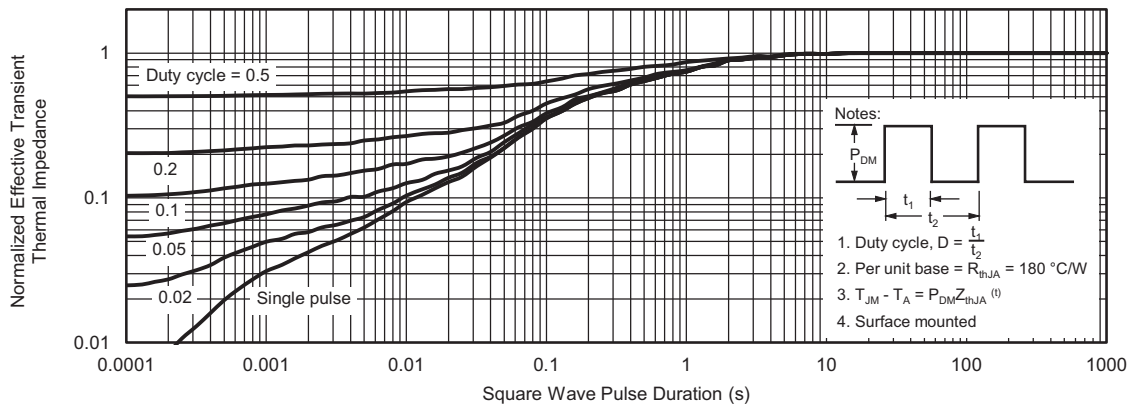
Threshold Voltage

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Safe Operating Area

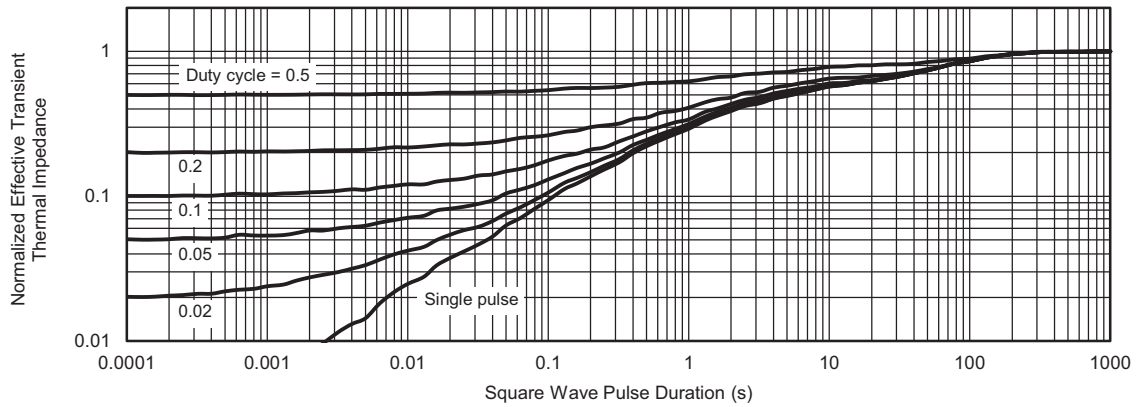
THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

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